

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)	PATENT APPLICATION
)	
Inventors: Jer-Shen Maa, Jong-Jan Lee,)	
Douglas J. Tweet and)	
Sheng Teng Hsu)	
)	
Serial No.: Not Yet Assigned)	Attorney Docket No.
)	SLA 0780
Filed: Herewith)	
)	
Title: METHOD OF MAKING)	
RELAXED SILICON-)	
GERMANIUM ON INSULATOR)	
VIA LAYER TRANSFER WITH)	
STRESS REDUCTION)	

Honorable Commissioner for Patents
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to 37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by the Examiner and made of record in the above-identified application.

9/30/03

Date

Respectfully submitted,

David C. Ripma
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1449A/PTO Rev. 10/95		U.S. Department of Commerce Patent and Trademark Office		Compleat If Known	
LIST OF PRIOR ART CITED BY APPLICANT (use as many sheets as necessary)				Application Number	
				Filing Date	September 30, 2003
				First Named Inventor	Jer-shen Maa
				Group Art Unit	
				Examiner Name	
Sheet	1	of	1	Attorney Docket No.	SLA.0780

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source.	T ²
		K. RIM <i>et al.</i> , <i>Strained Si for sub-100 nm MOSFETs</i> , Proceedings of the 3rd International Conference on SiGe Epitaxy and Heterostructures, Sante Fe, New Mexico, March 9-12, 2002, p125.	
		M. BRUEL <i>et al.</i> , <i>Smart-Cut: A New Silicon On Insulator Material Technology Based on Hydrogen Implantation and Wafer Bonding</i> , Jpn. J. Appl. Phys., Vol. 36, 1636 (1997).	
		Z.-Y. CHENG <i>et al.</i> , <i>SiGe-on insulator (SGOI): Substrate Preparation and MOSFET Fabrication for Electron Mobility Evaluation</i> , 2001 IEEE International SOI Conference Proceedings p 13.	
		Z. CHENG <i>et al.</i> , <i>Relaxed Silicon-Germanium on Insulator Substrate by Layer Transfer</i> , Journal of Electronics Materials, Vol. 30, No. 12, 2001, L37.	
		G. TARASCHI <i>et al.</i> , <i>Relaxed SiGe on Insulator Fabricated via Wafer Bonding and Layer Transfer: Etch-back and Smart-Cut Alternatives</i> , Electrochemical Society Proceedings Vol. 2001-3, p27.	
		L.-J. HUANG <i>et al.</i> , <i>Carrier Mobility Enhancement in Strained Si-on-Insulator Fabricated by Wafer Bonding</i> , 2001 Symposium on VLSI Technology Digest of Technical Papers, p 57.	
		T.A. LANGDO <i>et al.</i> , <i>Preparation of Novel SiGe-Free Strained Si on Insulator Substrates</i> , 2002 IEEE International SOI Conference Proceedings, October 2001, p211.	
		H. YIN <i>et al.</i> , <i>Strain relaxation of SiGe islands on compliant oxide</i> , Journal of Applied Physics, 91, 2002, 9718.	

Examiner Signature		Date Considered	
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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²Applicant is to place a check mark here if English language Translation is attached.